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			Application Number	10/628,188	_	
IN	NEORMATION DISCLO	SURE	Filing Date	July 28, 2003		
			First Named Inventor	Fechko et al.	_	
			Art Unit	1765		
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aat	1 0	1	Attorney Docket Number	5000.302	,	

U. S. PATENT DOCUMENTS **Publication Date** Pages, Columns, Lines, Where Name of Patentee or Examiner Cite **Document Number** Initials\* No.1 MM-DD-YYYY Applicant of Cited Document Relevant Passages or Relevant Number-Kind Code<sup>2 (# known)</sup> Figures Appear US-08-30-2001 Tsvetkov, Valeri M) 1 2001/017374 A1 2 6,497,764 B2 12-24-2002 M) Kuhn et al. US US-US-US-US-US-US-US-US-US-US-US-US-US-

	FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> Number * Kind Code <sup>5</sup> (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	™		
M	3	GB 772,691 A	04-17-1957	Philips Electrical Ind.	,.			
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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(Use as many sheets as necessary)

Sheet 1 of 2 Attorney Docket Number

			U. S. PATENT		
Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2</sup> (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
M)	1	<sup>US-</sup> 6,218,680	04-17-2001	Carter, Jr. et al.	
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	3	<sup>US-</sup> 6,113,451	09-05-2000	Hobart et al.	
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<u> </u>	5	<sup>US-</sup> 5,611,955	03-18-1997	Barrett et al.	
1	6	<sup>US-</sup> RE 34,861	02-14-1995	Davis et al.	
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MO	10	WO 90/00817 A1	01-25-1990	Raychem Limited		П			
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				Art Unit	1765	
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	NON PATENT LITERATURE DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Ť²						
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